Applicant: Hackenberger et al. Attorney's Docket No.: 12406-220US1 / P2004,0327

Serial No.: 10/599,949 I.A. Filed: April 21, 2005

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electrodes) of surface wave elements and bond pads which are in electrical contact therewith can be produced especially simply using variations of the procedure as per the invention. The electrically conducting microstructures of surface wave elements include, for instance, aluminium aluminum, while the bond pads which are in contact with them may, for instance, include gold.

Please add the following new header on page 11, at line 16:

## BRIEF DESCRIPTION OF THE FIGURES

Please add the following new header on page 11, at line 36:

## **DETAILED DESCRIPTION**

Please amend the following paragraph starting on page 12 at line 7, as follows: Subsequently, in process step B) as shown in Figure 1B, a mask structure 20 is applied to the second layer 15. This mask structure 20 herein possesses a geometrically formed area 20A, below which the bond pad is formed. Furthermore, the mask structure 20 has line-shaped linear structures 20B which originate from the area 20A, and which, in the event of contacts being produced, serve for structuring the later contact lines from the first layer 10. These line-formed linear structures of the mask structure 20 can be in the form of grates.

Please amend the following paragraph starting on page 13 at line 7, as follows:

This can, for instance, be accomplished by drying the mask structure so that the watery cleaners which were used to flush out the corrosive medium which was utilized in process step C) are removed. The eorrosive etching medium can, for instance, include wet chemical etching agents. For drying, the entire arrangement of the mask structure, both layers as well as the substrate, can be placed in a centrifuge device, wherein it is particularly advantageous to lower the undercut areas of the mask structure 20 onto the first layer 10 at the same time. Lowering the